

N-channel 30 V 2.1 m Ω logic level MOSFET in D2PAK

Rev. 1 — 20 March 2012

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1]	-	-	100	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	211	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>		-	2.51	2.9	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u>		-	1.79	2.1	mΩ
Dynamic	characteristics						
Q _{GD}	gate-drain charge	V_{GS} = 4.5 V; I_{D} = 25 A; V_{DS} = 15 V;		-	16	-	nC
Q _{G(tot)}	total gate charge	see Figure 13; see Figure 14		-	55	-	nC
Avalanch	e ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω ; unclamped		-	-	555	mJ

[1] Continuous current is limited by package.

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Ordering information Type number Package Name Description Version PSMN2R0-30BL D2PAK plastic single-ended surface-mounted package (D2PAK); 3 leads SOT404 (one lead cropped)

4. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN2R0-30BL	PSMN2R0-30BL

N-channel 30 V 2.1 m Ω logic level MOSFET in D2PAK

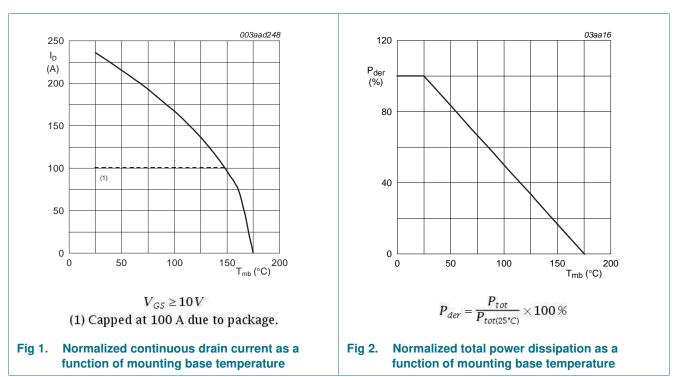
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

	_					
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	30	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3		-	943	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	211	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dr	ain diode					
ls	source current	T _{mb} = 25 °C	<u>[1]</u>	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	943	А
Avalanche	ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω; unclamped		-	555	mJ

[1] Continuous current is limited by package.



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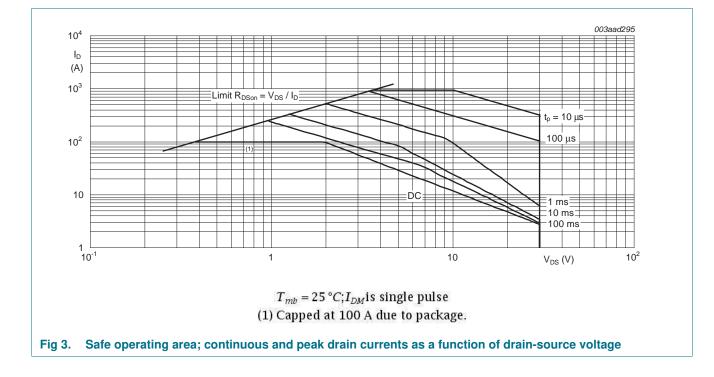


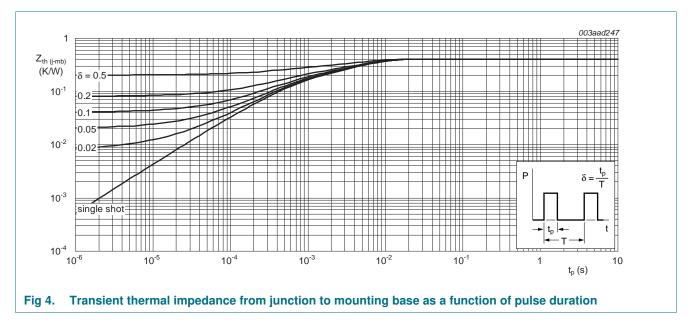
Table C

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Thermal characteristics 6.

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Table 6.	Inermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.41	0.71	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	maximum foot print; mounted on a printed circuit board	-	50	-	K/W



N-channel 30 V 2.1 mΩ logic level MOSFET in D2PAK

7. Characteristics

Table 7. Characteristics

Tested to JEDEC standards where applicable.

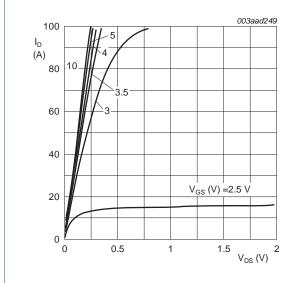
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	30	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	1.3	1.7	2.15	V
		$\label{eq:ID} \begin{split} I_D = 1 \mbox{ mA; } V_{DS} = V_{GS}; T_j = 175 \mbox{ °C}; \\ see \mbox{ Figure 10} \end{split}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	2.45	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	3	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	70	μA
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R _{DSon} drain-source on-state resistance	drain-source on-state resistance	V_{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u>	-	2.47	2.9	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	-	3.4	4	mΩ
	V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	-	2.51	2.9	mΩ	
	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 11</u>	-	1.79	2.1	mΩ	
R _G	gate resistance	f = 1 MHz	-	0.78	-	Ω
Dynamic o	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	107	-	nC
		I_D = 25 A; V_{DS} = 15 V; V_{GS} = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	117	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	55	-	nC
Q _{GS}	gate-source charge	see Figure 13; see Figure 14	-	17	-	nC
\sim						nC
GS(th)	pre-threshold gate-source charge		-	11	-	no
	pre-threshold gate-source charge post-threshold gate-source charge		-	11 6	-	nC
Q _{GS(th-pl)}	post-threshold gate-source				-	
Q _{GS(th-pl)} Q _{GD}	post-threshold gate-source charge	I _D = 25 A; V _{DS} = 25 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	- - -	6	- - -	nC
Q _{GS(th-pl)} Q _{GD} V _{GS(pl)}	post-threshold gate-source charge gate-drain charge			6 16	- - - -	nC nC
Q _{GS(th-pl)} Q _{GD} V _{GS(pl)} C _{iss}	post-threshold gate-source charge gate-drain charge gate-source plateau voltage	see Figure 14		6 16 2.6	-	nC nC V
Q _{GS} (th-pl) Q _{GD} V _{GS} (pl) C _{iss} C _{oss}	post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance	see <u>Figure 14</u> V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	- - - - -	6 16 2.6 6810	- - -	nC nC V pF
Q _{GS} (th-pl) Q _{GD} V _{GS} (pl) C _{iss} C _{oss} C _{rss}	post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance	see <u>Figure 14</u> V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	- - - - - - - -	6 16 2.6 6810 1410		nC nC V pF pF
Q _{GS} (th-pl) Q _{GD} V _{GS} (pl) C _{iss} C _{oss} C _{rss}	post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance	see Figure 14 $V_{DS} = 15 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see Figure 15}$	- - - - - - - - - - -	6 16 2.6 6810 1410 650	- - - -	nC NC V pF pF
Q _{GS} (th) Q _{GS} (th-pl) Q _{GD} V _{GS} (pl) C _{iss} C _{oss} C _{rss} t _d (on) t _r t _d (off)	post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance turn-on delay time	see Figure 14 $V_{DS} = 15 V; V_{GS} = 0 V; f = 1 MHz;$ $T_j = 25 \text{ °C}; \text{ see Figure 15}$ $V_{DS} = 15 V; R_L = 0.5 \Omega; V_{GS} = 4.5 V;$	- - - - - - - - - - - - - - -	6 16 2.6 6810 1410 650 63	- - - - -	nC nC V pF pF pF ns

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Table 7. Characteristics ...continued

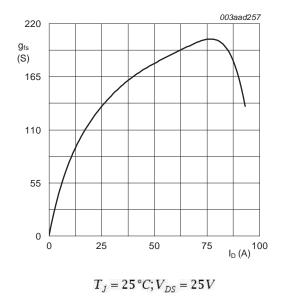
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Source-dr	ain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 16</u>	-	0.76	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	49	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 15 V$	-	66	-	nC

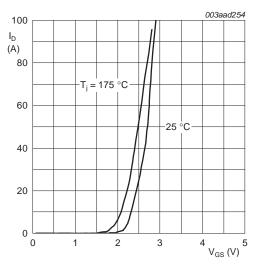


 $T_j = 25 \,^{\circ}C$



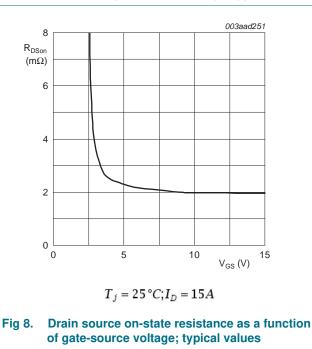




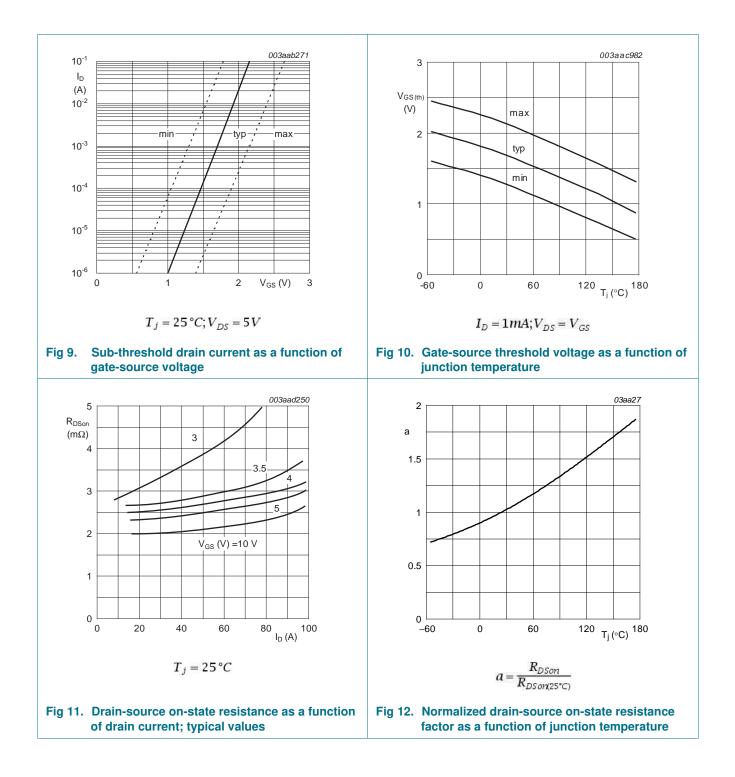




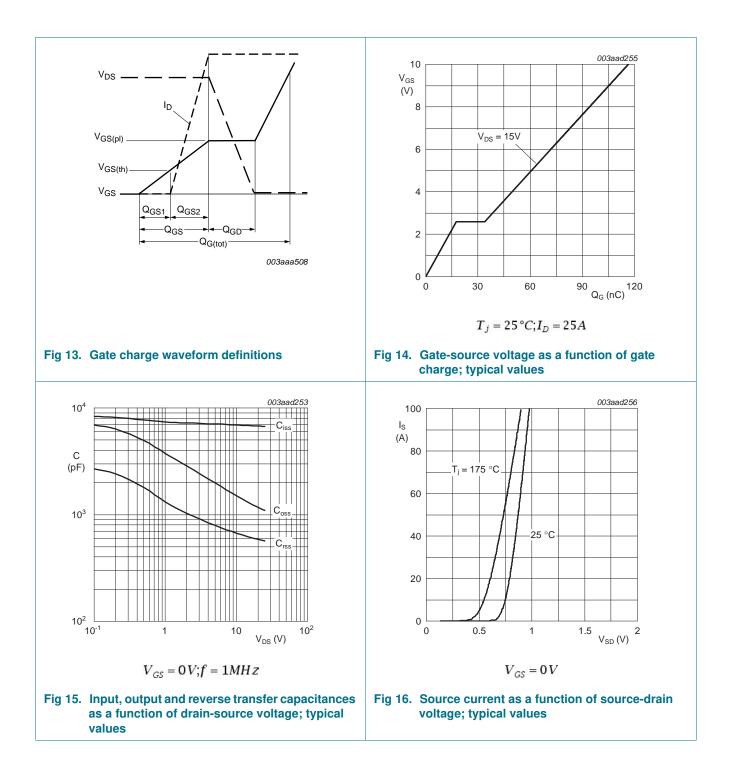




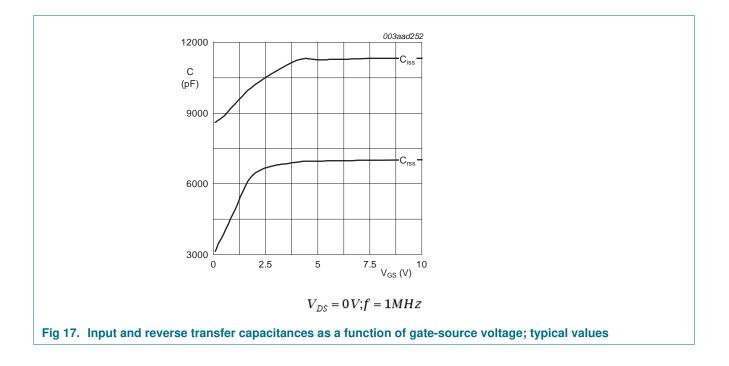
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8. Package outline

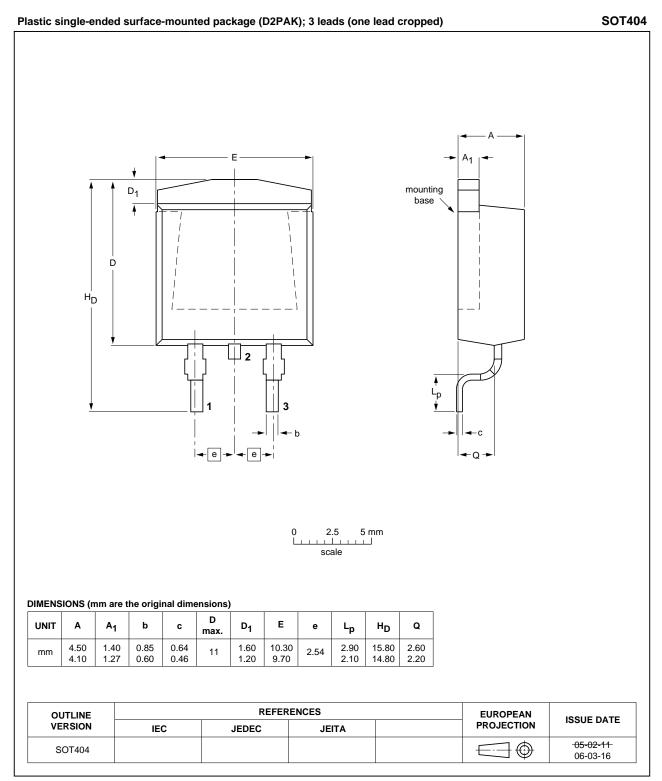


Fig 18. Package outline SOT404 (D2PAK)

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9. Revision history

Table 8. Revision h	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PSMN2R0-30BL v.1	20120320	Product data sheet	-	-			

N-channel 30 V 2.1 mΩ logic level MOSFET in D2PAK

10. Legal information

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Document status ^[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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